

HZS Series

Silicon Planar Zener Diode for Stabilized Power Supply

REJ03G0184-0500 Rev.5.00 Oct 29, 2007

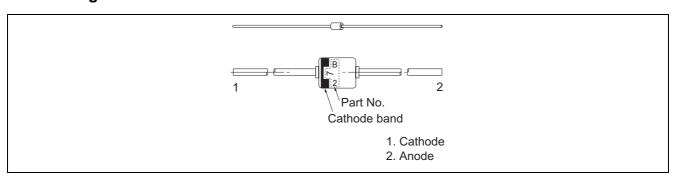
Features

- Low leakage, low zener impedance and maximum power dissipation of 400 mW are ideally suited for stabilized power supply, etc.
- Wide spectrum from 1.6 V through 38 V of zener voltage provide flexible application.
- Suitable for 5mm-pitch high speed automatic insertion.

Ordering Information

Part No.	Cathode band	Package Name	Package Code	
HZS Series	Lake blue	MHD	GRZZ0002ZC-A	

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Power dissipation	Pd	400	mW
Junction temperature	Tj	200	°C
Storage temperature	Tstg	−55 to +175	°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

		Zener Voltage			Reverse	e Current	Dynamic F	Dynamic Resistance	
				Test		Test	-	Test	
		V _z (V)* ¹	Condition	I _R (μΑ)	Condition	r _d (Ω)	Condition	
Туре	Grade	Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)	
HZS2	A1	1.6	1.8	5	25	0.5	100	5	
	A2	1.7	1.9						
	А3	1.8	2.0						
	B1	1.9	2.1	5	5	0.5	100	5	
	B2	2.0	2.2						
	В3	2.1	2.3						
	C1	2.2	2.4						
	C2	2.3	2.5						
	C3	2.4	2.6						
HZS3	A1	2.5	2.7	5	5	0.5	100	5	
	A2	2.6	2.8						
	А3	2.7	2.9						
	B1	2.8	3.0						
	B2	2.9	3.1						
	В3	3.0	3.2						
	C1	3.1	3.3						
	C2	3.2	3.4						
	C3	3.3	3.5						
HZS4	A1	3.4	3.6	5	5	1.0	100	5	
	A2	3.5	3.7						
	А3	3.6	3.8						
	B1	3.7	3.9						
	B2	3.8	4.0						
	B3	3.9	4.1						
	C1	4.0	4.2						
	C2	4.1	4.3						
	C3	4.2	4.4						
HZS5	A1	4.3	4.5	5	5	1.5	100	5	
	A2	4.4	4.6						
	А3	4.5	4.7						
	B1	4.6	4.8						
	B2	4.7	4.9						
	В3	4.8	5.0						

Note: 1. Tested with DC.

 $(Ta = 25^{\circ}C)$

		Zener Voltage		Revers	e Current	Dynamic Resistance		
				Test		Test		Test
		V _z (V)* ¹	Condition	I _R (μ A)	Condition	r_d (Ω)	Condition
Type	Grade	Min	Max	Iz (mA)	Max	V _R (V)	Max	I _Z (mA)
HZS5	C1	4.9	5.1	5	5	1.5	100	5
	C2	5.0	5.2					
	C3	5.1	5.3					
HZS6	A1	5.2	5.5	5	5	2.0	40	5
	A2	5.3	5.6					
	A3	5.4	5.7					
	B1	5.5	5.8					
	B2	5.6	5.9					
	B3	5.7	6.0					
	C1	5.8	6.1					
	C2	6.0	6.3					
	C3	6.1	6.4					
HZS7	A1	6.3	6.6	5	1	3.5	15	5
	A2	6.4	6.7					
	А3	6.6	6.9					
	B1	6.7	7.0					
	B2	6.9	7.2					
	В3	7.0	7.3					
	C1	7.2	7.6					
	C2	7.3	7.7					
	C3	7.5	7.9					
HZS9	A1	7.7	8.1	5	1	5.0	20	5
	A2	7.9	8.3					
	А3	8.1	8.5					
	B1	8.3	8.7					
	B2	8.5	8.9					
	В3	8.7	9.1					
	C1	8.9	9.3					
	C2	9.1	9.5					
	C3	9.3	9.7					
HZS11	A1	9.5	9.9	5	1	7.5	25	5
	A2	9.7	10.1					
	A3	9.9	10.3]				
	B1	10.2	10.6]				
	B2	10.4	10.8]				
	B3	10.7	11.1	1				
	C1	10.9	11.3	†				
	C2	11.1	11.6	1				
	C3	11.4	11.9	†				
HZS12	A1	11.6	12.1	5	1	9.5	35	5
1.2012	A2	11.9	12.4	†		3.0		
	A3	12.2	12.7	1				
	B1	12.4	12.7					
	-			-				
	B2	12.6	13.1	-				
L	B3 Tested wit	12.9	13.4	1				1

Note: 1. Tested with DC.

 $(Ta = 25^{\circ}C)$

		Zener Voltage		age	Revers	e Current	Dynamic Resistance	
				Test		Test	-	Test
		V _z (V)* ¹	Condition	I _R (μ A)	Condition	r_d (Ω)	Condition
Type	Grade	Min	Max	Iz (mA)	Max	V _R (V)	Max	I _Z (mA)
HZS12	C1	13.2	13.7	5	1	9.5	35	5
	C2	13.5	14.0					
	C3	13.8	14.3					
HZS15	-1	14.1	14.7	5	1	11.0	40	5
	-2	14.5	15.1					
	-3	14.9	15.5					
HZS16	-1	15.3	15.9	5	1	12.0	45	5
	-2	15.7	16.5					
	-3	16.3	17.1					
HZS18	-1	16.9	17.7	5	1	13.0	55	5
	-2	17.5	18.3					
	-3	18.1	19.0					
HZS20	-1	18.8	19.7	2	1	15.0	60	2
	-2	19.5	20.4					
	-3	20.2	21.1					
HZS22	-1	20.9	21.9	2	1	17.0	65	2
	-2	21.6	22.6					
	-3	22.3	23.3					
HZS24	-1	22.9	24.0	2	1	19.0	70	2
	-2	23.6	24.7					
	-3	24.3	25.5					
HZS27	-1	25.2	26.6	2	1	21.0	80	2
	-2	26.2	27.6					
	-3	27.2	28.6					
HZS30	-1	28.2	29.6	2	1	23.0	100	2
	-2	29.2	30.6					
	-3	30.2	31.6					
HZS33	-1	31.2	32.6	2	1	25.0	120	2
	-2	32.2	33.6]				
	-3	33.2	34.6]				
HZS36	-1	34.2	35.7	2	1	27.0	140	2
	-2	35.3	36.8]				
	-3	36.4	38.0]				

Notes: 1. Tested with DC.

2. Type No. is as follows; HZS2B1, HZS2B2, HZS36-3.

Main Characteristic

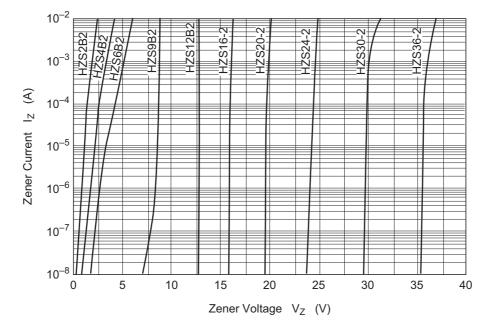


Fig.1 Zener current vs. Zener voltage

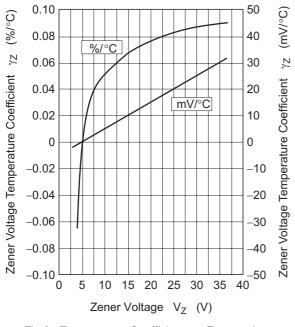


Fig.2 Temperature Coefficient vs. Zener voltage

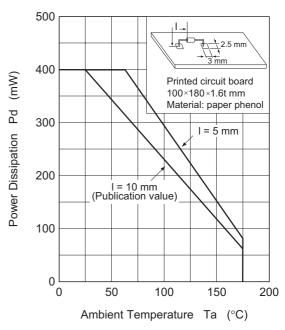
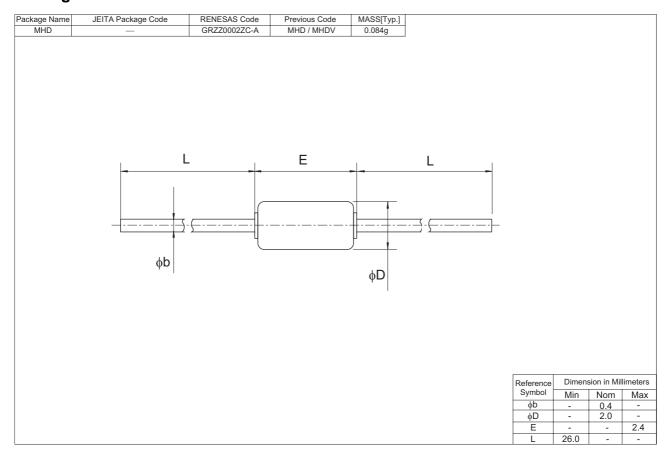


Fig.3 Power Dissipation vs. Ambient Temperature

Package Dimensions



Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc. 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510